

## Lista publicațiilor: Arsentiev Ivan N. (4), Descărcări - 0, Vizualizări - 161

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1. Arsentiev, Ivan. Bobyl, A.. Tarasov, Ilya. Boltovets, N.. Ivanov, V.. Beleaev, Alexander. Kamalov, A.. Konakova, Raisa. Kudryk, Ya.. Litvin, O.. Milenin, Viktor. Rusu, Emil. Properties of barrier contacts with nanosize TiB x layers to InP. *Semiconductors*. 2008, nr. , 777-782. ISSN 1063-7826.
2. Arsentiev, Ivan. Bobyl, A.. Boltovets, N.. Ivanov, V.. Konakova, Raisa. Kudryk, Ya.. Litvin, O.. Milenin, Viktor. Tarasov, Ilya. Beleaev, Alexander. Rusu, Emil. New manufacturing technology for InP epitaxial layers and properties of schottky diodes made on their basis. *International Crimean Conference "Microwave and Telecommunication Technology"*. Ediția 14. 2004. Sevastopol. Weber Publishing Co.. 528-529.
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